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## U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
MP	4,394,181	07/19/1983	Nicholas, K.H.	148	1.5	09/28/81
MP	5,145,794	09/08/1992	Kase, M., et al.	437	24	09/06/90
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## FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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## OTHER DOCUMENTS

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MP	Berti, M., et al., "Composition and Structure of Si-Ge Layers Produced by Ion Implantation and Laser Melting", <u>J. Mater. Res.</u> , Vol. 6, No. 10, pp. 2120-2126, (1991)
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MP	Myerson, B.S., et al., "SiGe-Channel Heterojunction p-MOSFET's", <u>IEEE Trans. on Electron Devices</u> , Vol. ED-41, No. 1, pp. 90-100, (Jan. 1994)
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MP	People, R., et al., "Calculation of critical layer thickness versus lattice mismatch for GeSi]-x/Si strained-layer heterostructures", <u>Appl. Phys. Lett.</u> , Erratum, 47, 322, (1985)
MP	Reedy, R., et al., "High Quality CMOS in Thin (100nm) Silicon on Sapphire", <u>IEEE Elect. Device Lett.</u> , Vol. 9, No. 1, pp 32-34, (Jan. 1988)
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\*Substitute Disclosure Statement Form (PTO-1449)

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